# NCP3712ASN, SZNCP3712ASN

# Over Voltage Protected High Side Switch

This switch is primarily intended to protect loads from transients by isolating the load from the transient energy rather than absorbing it.

#### **Features**

- Capable of Switching Loads of up to 200 mA without External Rboost
- Switch Shuts Off in Response to an Over Voltage Input Transient
- Features Active Turn Off for Fast Input Transient Protection
- Flexible Over Voltage Protection Threshold Set with External Zener
- Automatic Recovery after Transient Decays Below Threshold
- Withstands Input Transients up to 105 V Peak
- Guaranteed Off State with Enbl Input
- ESD Resistant in Accordance with the 2000 V Human Body Model
- Extremely Low Saturation Voltage
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

#### **Applications Include:**

- High Voltage Transient Isolation
- Power Switching to Electronic Modules
- DC Power Distribution in Line Operated Equipment
- Buffering Sensitive Circuits from Poorly Regulated Power Supplies
- Pre-conditioning of Voltage Regulator Input Voltage

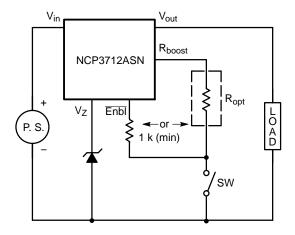


Figure 1. Typical Application Circuit



#### ON Semiconductor®

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MARKING DIAGRAM



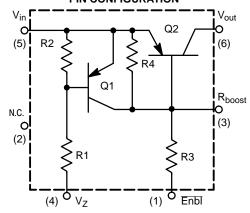
SC-74 CASE 318F



BAG = Device Code
M = Date Code

= Pb-Free Package(Note: Microdot may be in either location)

INTERNAL CIRCUIT DIAGRAM/ PIN CONFIGURATION



## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NCP3712ASNT1G	SC-74	3000 / Tape &
SZNCP3712ASNT1G	(Pb-Free)	Reel
NCP3712ASNT3G	SC-74	10,000 / Tape &
SZNCP3712ASNT3G	(Pb-Free)	Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### NCP3712ASN, SZNCP3712ASN

**MAXIMUM RATINGS** ( $T_J = 25^{\circ}C$  unless otherwise noted) (Note 1)

Rating		Symbol	Value	Unit
Input-to-Output Voltage		V <sub>io</sub>	105	V
Reverse Input-to-Vz. Voltage		V <sub>in(rev)</sub>	-9.0	V
Reverse Input-to-Rboost Voltage		V <sub>in(rev)</sub>	-5.0	V
Output Load Current – Continuous		I <sub>load</sub>	-300	mA
Enbl Input Current – Continuous		I <sub>enbl</sub>	5.0	mA
Vz Input Current – Continuous		Iz	3.0	mA
Rboost Input Current – Continuous		I <sub>boost</sub>	10	mA
Junction Temperature		TJ	125	°C
Operating Ambient Temperature Range		T <sub>A</sub>	-40 to +85	°C
Storage Temperature Range		T <sub>stg</sub>	-65 to +150	°C
Device Power Dissipation (Minimum Footprint)		P <sub>D</sub>	300	mW
Derate Above 25°C		_	2.4	mW/°C
Latchup Performance:	Positive Negative	I <sub>Latchup</sub>	200 200	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

This device contains ESD protection and exceeds the following tests: Human Body Model 1500 V per MIL-STD-883, Method 3015. Machine Model Method 150 V.

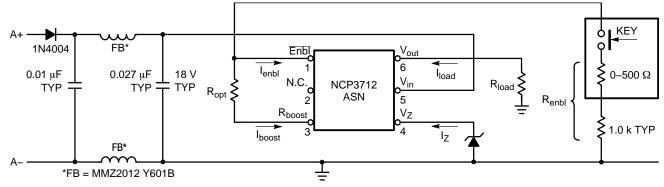


Figure 2. Typical Applications Circuit for Load Dump Transient Protection

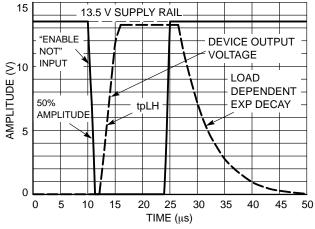


Figure 3. Enable NOT Switching Waveforms

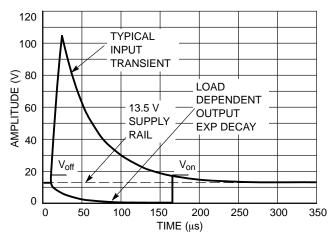


Figure 4. Load Dump Waveforms

## NCP3712ASN, SZNCP3712ASN

**ELECTRICAL CHARACTERISTICS** ( $V_{in}$  = 12.5  $V_{DC}$  Ref to Gnd,  $T_A$  = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	<u> </u>				
Input-Output Breakdown Voltage (@ I <sub>out</sub> = 200 μA)	V <sub>(BRio)</sub>	105	_	_	Vdc
Output Reverse Breakdown Voltage (@ I <sub>out</sub> = -1.0 mA Pulse)	V <sub>(-BRout)</sub>	_	-0.7	_	Vdc
Output Leakage Current (V <sub>in</sub> = V <sub>enbl</sub> = 30 V, T <sub>A</sub> = 25°C)	I <sub>load(off)</sub>	_	-	-100	μAdc
Guaranteed "Off" State "ENBL NOT" Voltage ( $I_O \le 100 \ \mu A$ )	V <sub>enbl(off)</sub>	13	-	_	Vdc
Required "Off" State $I_z$ Current ( $R_{load} = 100 \Omega$ )	I <sub>z(off)</sub>	150	-	_	μAdc
$V_{in(off)}$ (V <sub>z</sub> = 16 V, I <sub>load</sub> = 100 mA, R <sub>enbl</sub> = 1500 $\Omega$ )	V <sub>off</sub>	15.5	-	18.7	Vdc
ON CHARACTERISTICS					
Input–Output On Voltage (I <sub>o</sub> = 100 mA, I <sub>enbl</sub> = –3.0 mA)	V <sub>io(on)</sub>	_	0.2	0.5	Vdc
	l <sub>o(on)</sub>	- - -	- - -	-200 -200 -300	mAdc
$V_{in(on)}$ (V <sub>z</sub> = 16 V, I <sub>load</sub> = 100 mA, R <sub>enbl</sub> = 1500 $\Omega$ )	V <sub>on</sub>	8.5	_	10.5	Vdc
"ENBL NOT" Input Current (I <sub>o</sub> = 100 mA, $V_{io(on)}$ = 0.35 Vdc, $R_{enbl}$ = 1500 $\Omega$ )	lenbl	_	_	-1.0	mAdc
SWITCHING CHARACTERISTICS	<u>.</u>		•		
Propagation Delay Time: Hi to Lo Prop Delay; Fig. 3 (V <sub>in</sub> = V <sub>enbl</sub> = 13.5 V) Lo to Hi Prop Delay; Fig. 3 (V <sub>in</sub> = 13.5 V, V <sub>enbl</sub> = 0 V)	t <sub>PHL</sub>	_ _	1.5 1.5	_ _	μS
Transition Times: Fall Time; Fig. 4 ( $V_{in} = V_{enbl} = 13.5 \text{ V}$ ) Rise Time; Fig. 4 ( $V_{in} = V_{enbl} = 0 \text{ V}$ )	t <sub>f</sub> t <sub>r</sub>	_ _	75 400	_ _	ηS
INTERNAL RESISTORS	·				·
Input Leakage Resistor	R2	7.0	10	13	kΩ
Input Resistor	R1	3.3	4.7	6.1	kΩ
Output Leakage Resistor	R4	1.4	2.4	3.2	kΩ
Enable Input Resistor	R3	1.4	2.4	3.2	kΩ

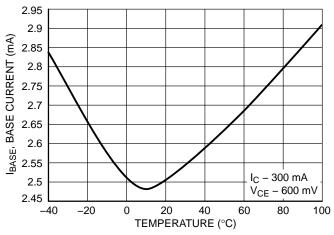
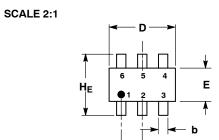


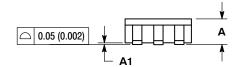
Figure 5. Q2 Base Current vs Temperature with Pin 4 Open

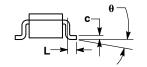


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**DATE 08 JUN 2012** 



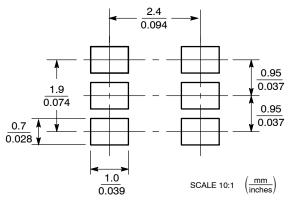




- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH
- CONTROLLING DIMENSION: INCH.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
  THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
С	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. ANODE 6. CATHODE	STYLE 2: PIN 1. NO CONNECTION 2. COLLECTOR 3. EMITTER 4. NO CONNECTION 5. COLLECTOR 6. BASE	STYLE 3: PIN 1. EMITTER 1 2. BASE 1 3. COLLECTOR 2 4. EMITTER 2 5. BASE 2 6. COLLECTOR 1	STYLE 4: PIN 1. COLLECTOR 2 2. EMITTER 1/EMITTER 2 3. COLLECTOR 1 4. EMITTER 3 5. BASE 1/BASE 2/COLLECTOR 3 6. BASE 3	STYLE 5: PIN 1. CHANNEL 1 2. ANODE 3. CHANNEL 2 4. CHANNEL 3 5. CATHODE 6. CHANNEL 4	STYLE 6: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE

4. CATHODE 5. ANODE	4. NO CONNECTION 5. COLLECTOR	4. EMITTER 2 5. BASE 2	4. EMITTER 3 5. BASE 1/BASE 2/COLLECTOR 3	4. CHANNEL 3 5. CATHODE
6. CATHODE	6. BASE	6. COLLECTOR 1	6. BASE 3	6. CHANNEL 4
STYLE 7: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 8: PIN 1. EMITTER 1 2. BASE 2 3. COLLECTOR 2 4. EMITTER 2 5. BASE 1 6. COLLECTOR 1	STYLE 9: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 10: PIN 1. ANODE/CATHODE 2. BASE 3. EMITTER 4. COLLECTOR 5. ANODE 6. CATHODE	STYLE 11: PIN 1. EMITTER 2. BASE 3. ANODE/CATHODE 4. ANODE 5. CATHODE 6. COLLECTOR

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